

MJE700/701/702/703

Monolithic Construction With Built-in Base-Emitter Resistors

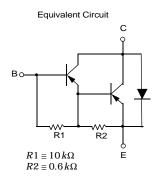
- High DC Current Gain : $h_{\mbox{\scriptsize FE}}\mbox{\scriptsize =}750$ (Min.) @ $I_{\mbox{\scriptsize C}}\mbox{\scriptsize =}-1.5$ and -2.0A DC
- Complement to MJE800/801/802/803



PNP Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Sym- bol	Parameter	Value	Unit s
V _{CBO}	Collector- Base Voltage : MJE700/701	- 60	V
	: MJE702/703	- 80	V
V _{CEO}	Collector-Emitter Voltage: MJE700/701	- 60	V
	: MJE702/703	- 80	V
V _{EBO}	Emitter- Base Voltage	- 5	V
I _C	Collector Current	- 4	Α
I _B	Base Current	- 0.1	Α
P _C	Collector Dissipation (T _C =25°C)	40	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage				
	: MJE700/701	$I_C = -10 \text{mA}, I_B = 0$	-60		V
	: MJE702/703		-80		V
I _{CEO}	Collector Cut-off Current				
	: MJE700/701	$V_{CE} = -60V, I_{B} = 0$		-100	μΑ
	: MJE702/703	$V_{CE} = -80V, I_{B} = 0$		-100	μΑ
I _{CBO}	Collector Cut-off Current	$V_{CB} = Rated BV_{CEO}, I_E = 0$		-100	μΑ
		$V_{CB} = Rated BV_{CEO}, I_E = 0$		-500	μΑ
		T _C = 100°C			
I _{EBO}	Emitter Cut-off Current	$V_{BE} = -5V, I_{C} = 0$		-2	mA
h _{FE}	DC Current Gain	-			
	: MJE700/702	$V_{CE} = -3V, I_{C} = -1.5A$	750		
	: MJE701/703	$V_{CE} = -3V, I_{C} = -2A$	750		
	: ALL DEVICES	$V_{CE} = -3V, I_{C} = -4A$	100		
V _{CF} (sat)	Collector-Emitter Saturation Voltage				
02	: MJE700/702	$I_C = -1.5A, I_B = -30mA$		-2.5	V
	: MJE701/703	$I_C = -2A$, $I_B = -40mA$		-2.8	V
	: ALL DEVICES	$I_C = -4A, I_B = -40mA$		-3	V
V _{BE} (on)	Base-Emitter On Voltage				
:	: MJE700/702	$V_{CE} = -3V, I_{C} = -1.5A$		-1.2	V
	: MJE701/703	$V_{CE} = -3V, I_{C} = -2A$		-2.5	V
	: ALL DEVICES	$V_{CE} = -3V, I_{C} = -4A$		-3	V

Typical Characteristics

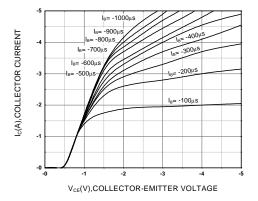


Figure 1. Static Characteristic

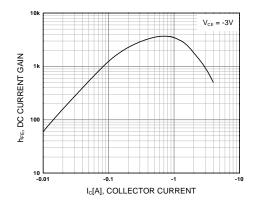


Figure 2. DC current Gain

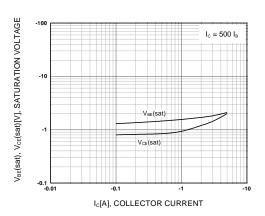


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

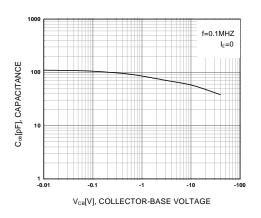


Figure 4. Collector Output Capacitance

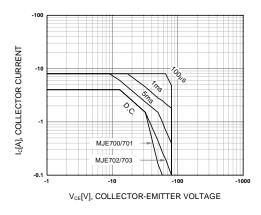


Figure 5. Safe Operating Area

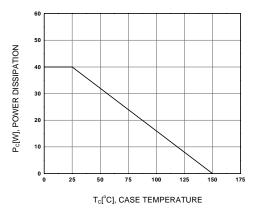
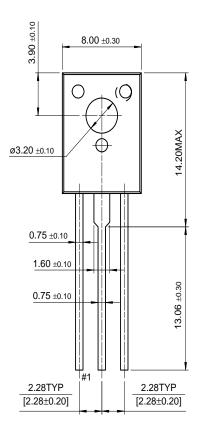


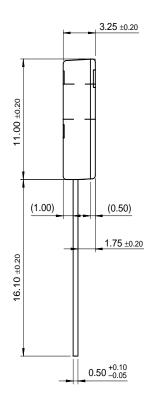
Figure 6. Power Derating

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Package Demensions

TO-126







Dimensions in Millimeters

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